

P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)			
- 30	0.0087 at $V_{GS} = -10 \text{ V}$	- 45 ^d	60			
- 30	0.0150 at $V_{GS} = -4.5 \text{ V}$	- 32	00			

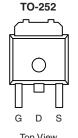
FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- 100 % R_q and UIS Tested

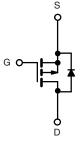


APPLICATIONS

- Power Switch
- Load Switch in High Current Applications
- DC/DC Converters



Drain Connected to Tab



P-Channel MOSFET

Ordering Information: SUD45P03-09-GE3 (Lead (Pb)-free and Halogen-free)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 30	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	1-	- 45 ^d		
Continuous Drain Current (1) = 130 °C)	T _C = 70 °C	I _D	- 42.5] _A	
Pulsed Drain Current		I _{DM}	- 100		
Avalanche Current		I _{AS}	- 35		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	61	mJ	
Mariana Barra Biratina	T _C = 25 °C	В	41.7 ^b	w	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	$ P_D$ $-$	2.1]	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	60	°C/W		
Junction-to-Case (Drain)	R _{thJC}	3	C/VV		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

SUD45P03-09

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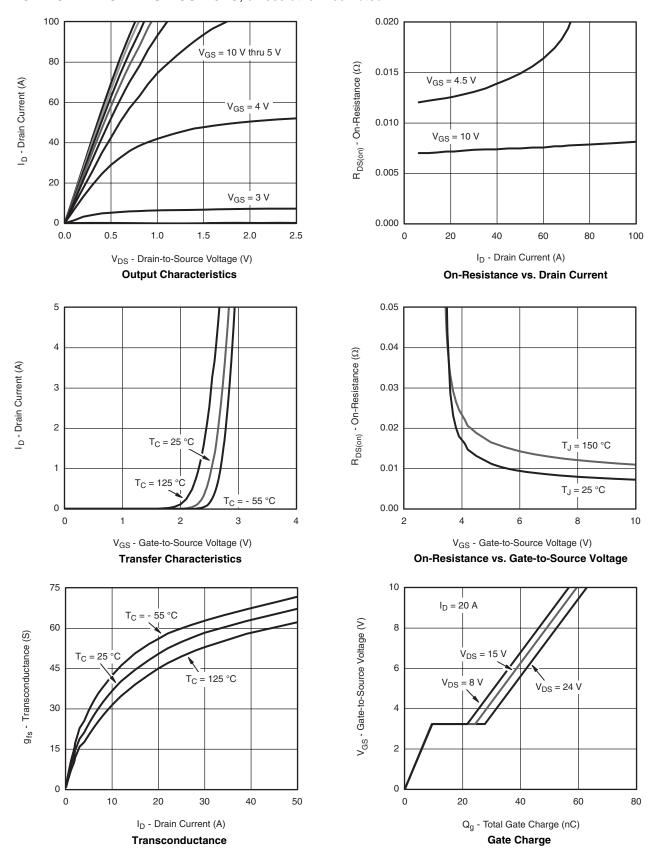
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 30		V		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1 - 2.5		V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		V _{DS} = - 30 V, V _{GS} = 0 V	: 0 V		1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 125 °C			50	50 μA 250	
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 150 °C			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 50			Α	
D : 0	В	V _{GS} = - 10 V, I _D = - 20 A		0.0072	0.0087	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 15 A		0.0125	0.0150		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 20 A		45		S	
Dynamic ^b							
Input Capacitance	C _{iss}			2700		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 15 V, f = 1 MHz		515			
Reverse Transfer Capacitance	C _{rss}			445			
Total Gate Charge ^c	Q_g			60	90	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -20 \text{ A}$		9.3			
Gate-Drain Charge ^c	Q _{gd}			15			
Gate Resistance	R _g	f = 1 MHz	0.5	2.5	5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			12	20		
Rise Time ^c	t _r	V_{DD} = - 15 V, R_{L} = 1.5 Ω		11	20	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω		40	60		
Fall Time ^c	t _f			12	20		
Drain-Source Body Diode Ratings ar	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	Is				- 45	_	
Pulsed Current	I _{SM}				- 100	А	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	٧	
Reverse Recovery Time	t _{rr}			27	40	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dI/dt = 100 A/μs		1.3	2	Α	
Reverse Recovery Charge	Q _{rr}			20	30	nC	

Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

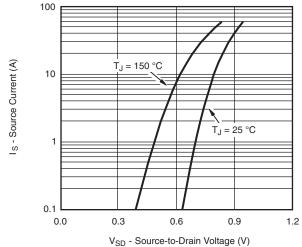
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

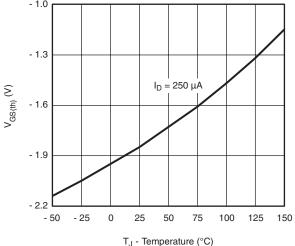




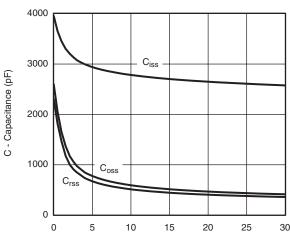
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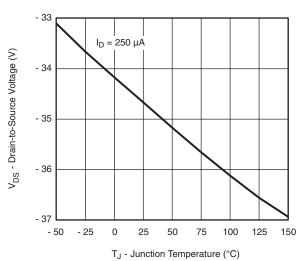
Source-Drain Diode Forward Voltage



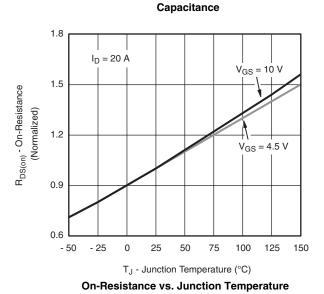
Threshold Voltage



V_{DS} - Drain-to-Source Voltage (V)

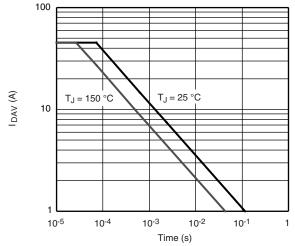


Drain Source Breakdown vs. Junction Temperature

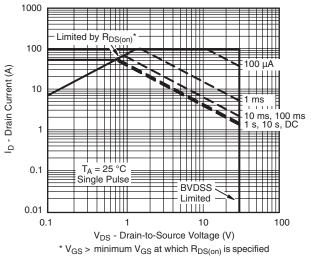


Current Derating

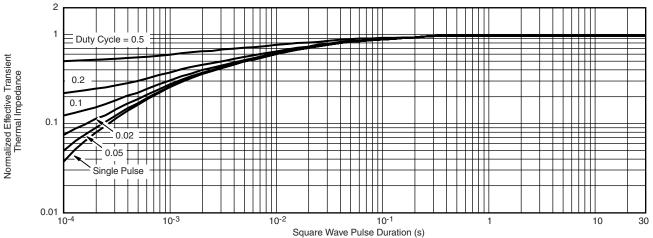
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Single Pulse Avalanche Current Capability vs. Time



 V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified **Safe Operating Area**

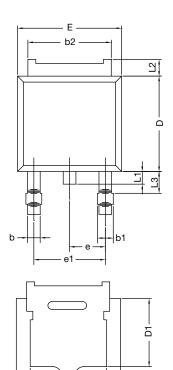


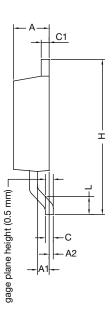
Normalized Thermal Transient Impedance, Junction-to-Case



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TO-252AA CASE OUTLINE



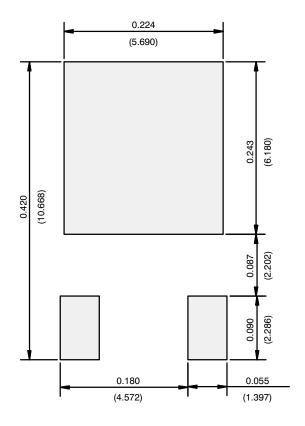


	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
A2	0.030	0.127	0.001	0.005
b	0.71	0.88	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.44	0.206	0.214
С	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.10	4.45	0.161	0.175
Е	6.48	6.73	0.255	0.265
E1	4.49	5.50	0.177	0.217
е	2.28	BSC 0.090 BSC		BSC
e1	4.57	BSC	0.180 BSC	
Н	9.65	10.41	0.380	0.410
L	1.40	1.78	0.055	0.070
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.040	0.060
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347				

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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